



SANYO Semiconductors

## DATA SHEET

# CPH6341 — P-Channel Silicon MOSFET

## General-Purpose Switching Device Applications

### Features

- Low ON-resistance.
- High-speed switching.
- 4V drive

### Specifications

**Absolute Maximum Ratings** at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		-30	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±20	V
Drain Current (DC)	I <sub>D</sub>		-5	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	-20	A
Allowable Power Dissipation	P <sub>D</sub>	When mounted on ceramic substrate (900mm <sup>2</sup> ×0.8mm)	1.6	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

**Electrical Characteristics** at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =-1mA, V <sub>GS</sub> =0V	-30			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V			-1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA	-1.2		-2.6	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-3A	2.8	4.8		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =-3A, V <sub>GS</sub> =-10V		45	59	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =-1.5A, V <sub>GS</sub> =-4.5V		71	100	mΩ
	R <sub>DS(on)3</sub>	I <sub>D</sub> =-1.5A, V <sub>GS</sub> =-4V		82	115	mΩ

Marking : YT

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**SANYO Semiconductor Co., Ltd.**

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# CPH6341

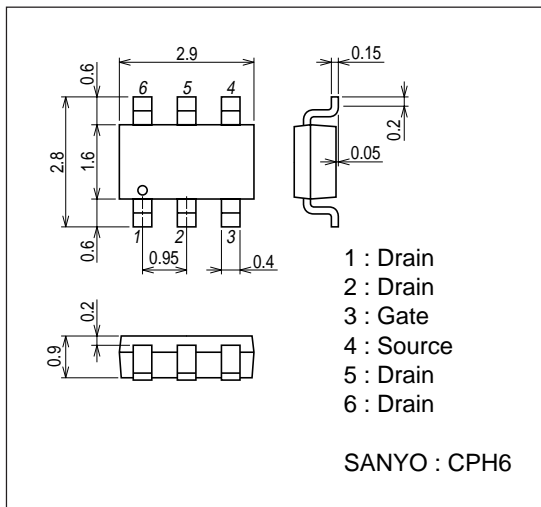
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V <sub>DS</sub> =-10V, f=1MHz		430		pF
Output Capacitance	Coss	V <sub>DS</sub> =-10V, f=1MHz		105		pF
Reverse Transfer Capacitance	Crss	V <sub>DS</sub> =-10V, f=1MHz		75		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit.		7.5		ns
Rise Time	t <sub>r</sub>	See specified Test Circuit.		26		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>	See specified Test Circuit.		45		ns
Fall Time	t <sub>f</sub>	See specified Test Circuit.		35		ns
Total Gate Charge	Qg	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-5A		10		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-5A		2.0		nC
Gate-to-Drain "Miller" Charge	Qgd	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-5A		2.5		nC
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-5A, V <sub>GS</sub> =0V	-0.87		-1.2	V

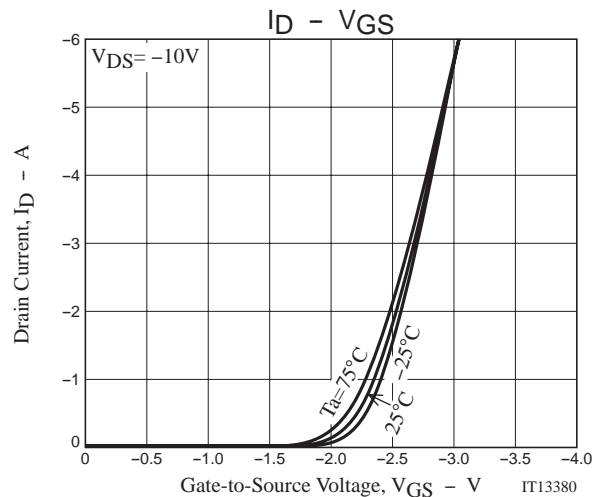
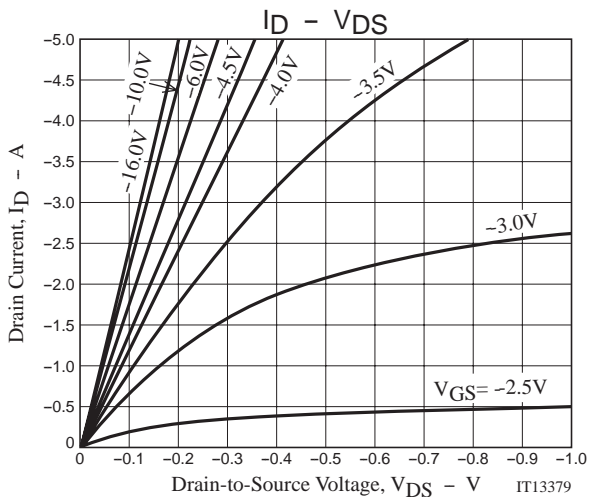
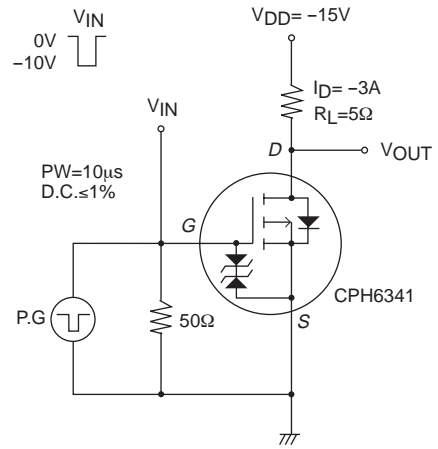
## Package Dimensions

unit : mm (typ)

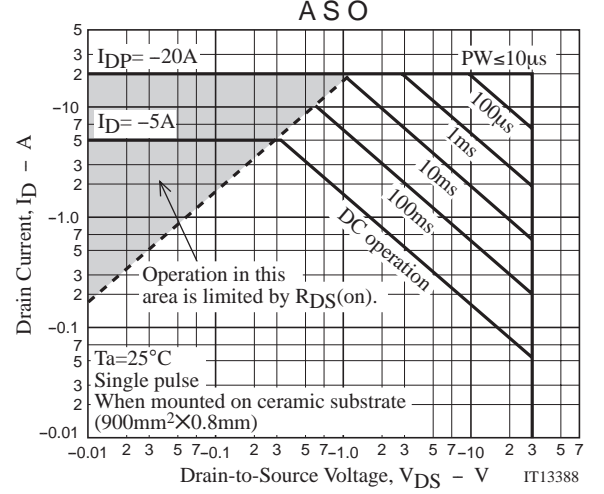
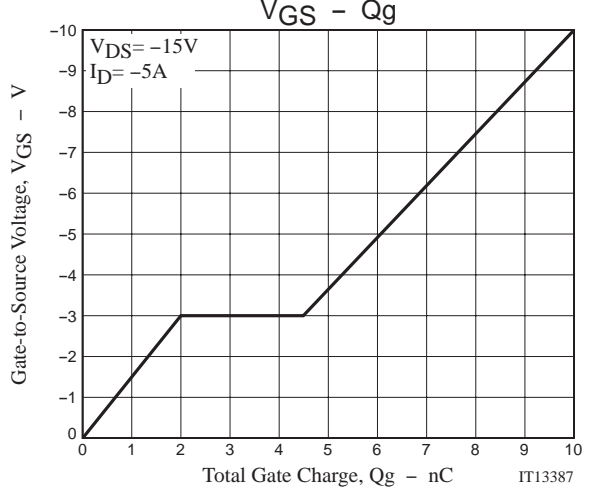
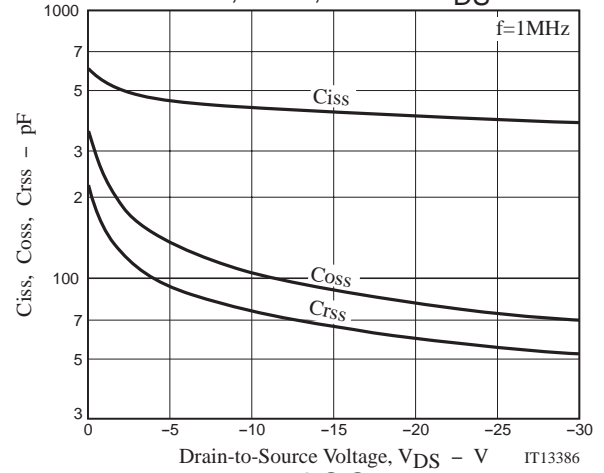
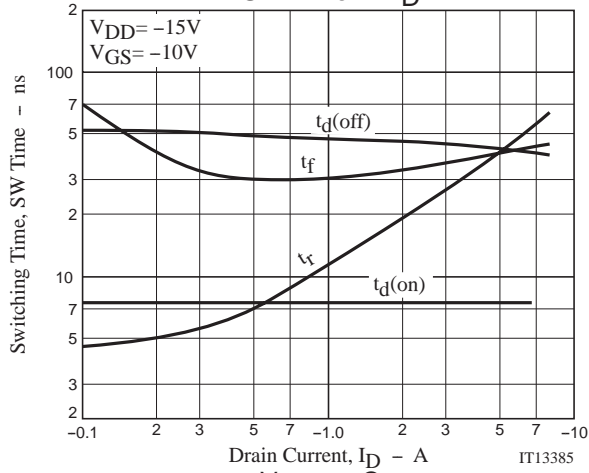
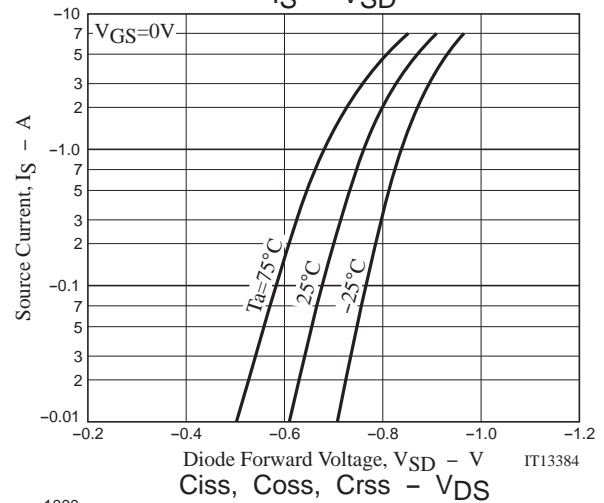
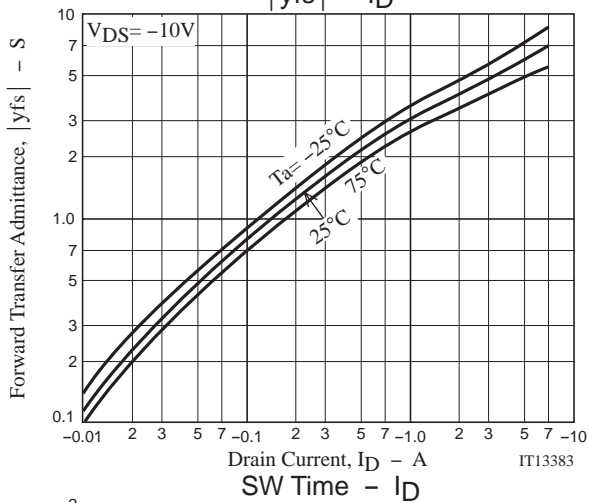
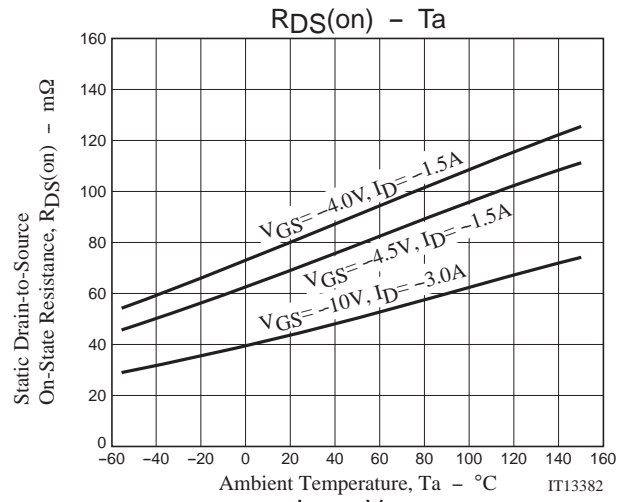
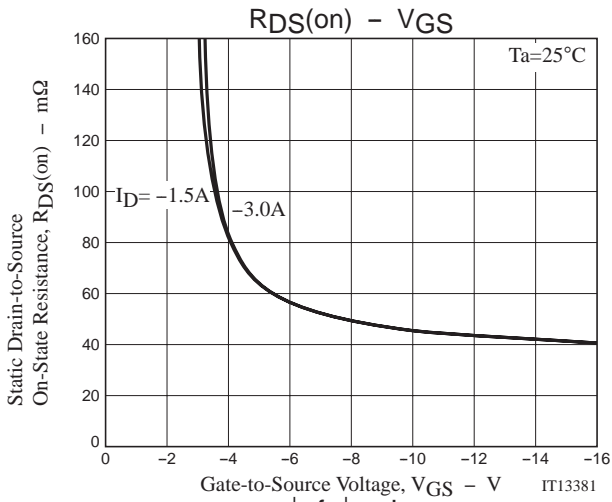
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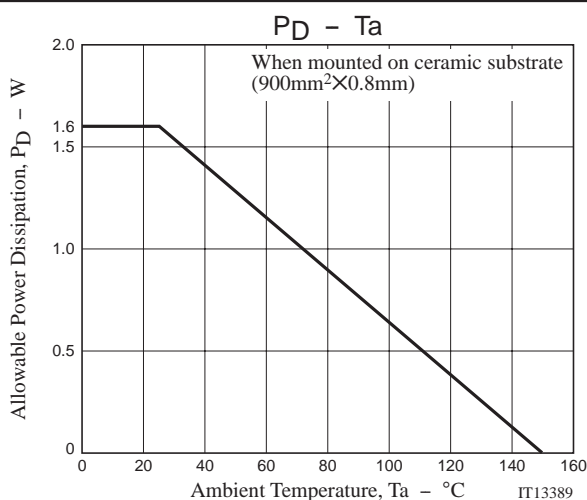


## Switching Time Test Circuit



# CPH6341





Note on usage : Since the CPH6341 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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